

GENERAL DESCRIPTION

OB2279 is a highly integrated current mode PWM control IC optimized for high performance, low standby power and cost effective offline fly back converter applications.

PWM switching frequency at normal operation is externally programmable and trimmed to tight range. At no load or light load condition, the IC operates in extended 'burst mode' to minimize switching loss. Lower standby power and higher conversion efficiency is thus achieved.

VDD low startup current and low operating current contribute to a reliable power on startup design with OB2279. A large value resistor could thus be used in the startup circuit for reduced power loss.

The internal slope com pensation im proves sy stem large signal stability and reduces the possible subharmonic oscillation at high PWM duty cycle output. Leading-edge blankin g on current sense input removes the signal glitch due to snubber circuit diode reverse r ecovery and greatly reduces the external component count and system cost in the design. OB2279 offers comprehensive protection coverage including Cy cle-by-Cycle current limiting(OCP), VDD Under Voltage Lockout(UVLO), VDD Over Voltage Protection(OVP), VDD Clamp, Gate Clamp, Over Load protection(OLP) and Over Tem perature protection (OTP), etc.

Different latch shutdown options are offered on OB2279 in different device version. V version has OVP Latch shutdown. T version supports both OVP and OTP latch shutdown. L version provides all OVP, OTP and OLP latch shutdown control

Excellent EMI perform ance is achieved with On-Bright proprietary frequency shuffling technique together with soft switching control at the totem pole gate drive output.

Tone energy at below 20KHZ is minim ized in operation. C onsequently, audio no ise is elim inated during operation.

OB2279 is offered in SOP-8 and DIP-8 packages.

FEATURES

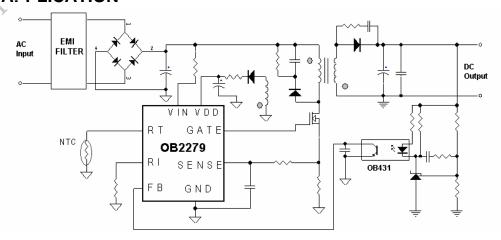
- On-Bright Proprietary Frequency Shuffling Technology for Improved EMI Performance
- Power On Soft Start
- Extended Burst Mode Control For Im proved Efficiency and Minimum Standby Power Design
- Audio Noise Free Operation
- External P rogrammable PWM Switching Frequency
- Internal Synchronized Slope Compensation
- Low VIN/V DD Startup Current(3uA) and Low Operating Current (2.3mA)
- Leading Edge Blanking on Current Sense Input
- Complete Protection Coverage with selectiv protections for Latch Shutdown
 - VDD Ov er Voltage Protection(OVP) Latch Shutdown
 - Over Tem perature Protection(OTP) Autorecovery or Latch Shutdown
 - Over Lead P rotection. (OLP) Aut o recovery or Latch Shutdown
 - o VDD Under Voltage Lockout with Hysteresis (UVLO)
 - Gate Output Voltage Clamp (16.5V)
- Built-in OCP Com pensation to Achieve Minimum OPP Variation over Universal AC Input Range.

APPLICATIONS

Offline AC/DC flyback converter for

- Adaptor
- Notebook Adaptor
- LCD Monitor/TV/PC/Set-Top Box Power Supplies
- Open-frame SMPS
- Printer Power

TYPICAL APPLICATION

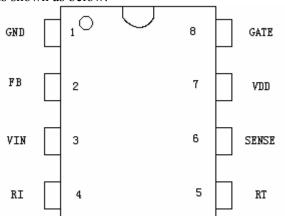




GENERAL INFORMATION

Pin Configuration

The pin map of OB2279 in DIP8 and SOP8 package is shown as below.



Ordering Information

Part Number	Description
OB2279AP-V	DIP8, V version with OVP
	Latch
OB2279AP-T	DIP8, T version with
	OVP/OTP latch
OB2279AP-L	DIP8, L version with
	OVP/OTP/OLP latch
OB2279CP-V	SOP8, V version with OVP
	latch
OB2279CP-T	SOP8, T version with
	OVP/OTP latch

OB2279CP-L	SOP8, L version with	
	OVP/OTP/OLP latch	

 $oldsymbol{Note:}$ All Devices are offered in Pb-free Package if not otherwise noted.

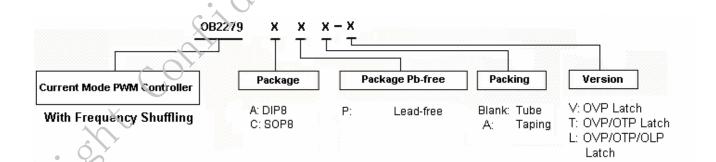
Package Dissipation Rating

Package	RθJA (°C/W)
DIP8	90
SOP8	150

Absolute Maximum Ratings

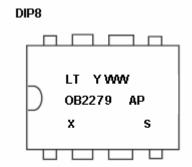
Parameter Value	. /// >
VDD Clamp Voltage	35 V
VDD Clamp Continuous	10 mA
Current	
V _{FB} Input Voltage	-0.3 to 7V
V _{SENSE} Input Voltage to Sense	-0.3 to 7V
Pin	
V _{RT} Input Voltage to RT Pin	-0.3 to 7V
V _{RI} Input Voltage to RI Pin	-0.3 to 7V
Min/Max Operating Junction	-20 to 150 °C
Temperature T _J	
Min/Max Storage Temperature	-55 to 150 °C
T_{stg}	
Lead Temperature (Soldering,	260 °C
10secs)	

Note: Stresses beyond those listed under "absolute maximum ratings" may cause permanent d amage to the de vice. These are stress ratings only, functional operation of the de vice at these or any othe r conditions bey ond those indicated under "recommended operating conditions" is not implied. Exposure to absolute maximum-rate d conditi ons for extende d periods may affect device reliability.





Marking Information



A: DIP8 Package

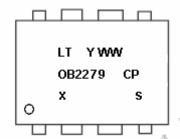
P: Pb-free Package Y: Year Code(0-9)

WW: Week Code(01-52)

X: Version

s: Internal Code

SOP8



C: SOP8 Package

P: Pb-free Package

Y: Year Code(0-9)

WW: Week Code (01-52)

X: Version

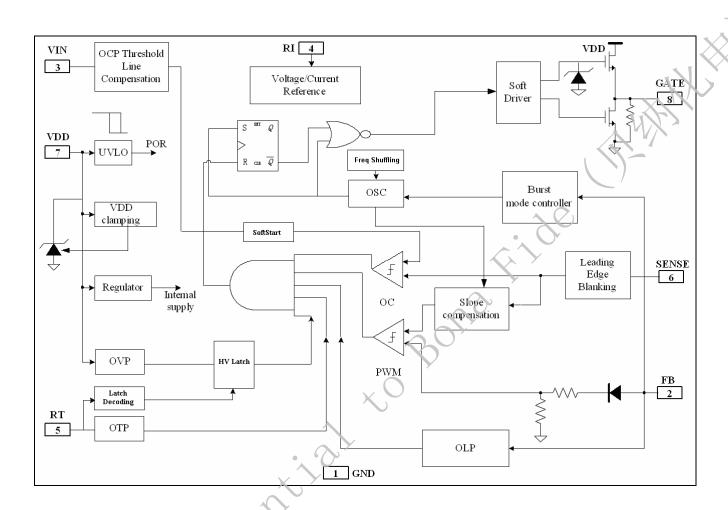
s: Internal Code

TERMINAL ASSIGNMENTS

Pin Num	Pin Name	I/O	Description
1 GND		P	Ground
2	FB	I	Feedback input pin. PWM duty cycle is determined by voltage level into this pin and current-sense signal level at Pin 6.
3	VIN	I	Connected through a large value resistor to rectified line input for Startup and line voltage sensing.
4	RI	I	Internal Oscillator frequency setting pin. A resistor connected between RI and GND sets, the PWM frequency.
5	RT	I	Dual function pin. Either connected through a NTC resistor to GND for over temperature shutdown control or used as latch shutdown control input.
6	SENSE	Ι	Current sense input pin. Connected to MOSFET current sensing resistor node.
7	VDD	P	DC power supply pin.
8	GATE	O	Fotem-pole gate drive output for power MOSFET.
	X CO		



BLOCK DIAGRAM



RECOMMENDED OPERATING CONDITION

VDD VDD Supply Voltage 11.5 25 V RI RI Resistor Value 100 133 Kohm T _A Operating Ambient Temperature -20 85 °C	Symbol Parar	neter	Min	Max	Unit
RI RI Resistor Value 100 133 Kohm	VDD VDD	Supply Voltage	11.5	25	V
T _A Operating Ambient Temperature -20 85 °C	RI		100	133	Kohm
	T_{A}	Operating Ambient Temperature	-20	85	°C
	X				
	. 6				
	. 4				
	35,70				
	55				



ELECTRICAL CHARACTERISTICS

 $(T_A = 25^{\circ}C \text{ if not otherwise noted})$

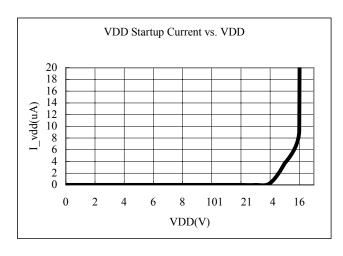
Symbol Parameter	r	Test Conditions	Min	Тур	Max	Unit
Supply Voltage (V			•	<u> </u>		- 1
I_VDD_Startup	VDD Start up Current	VDD=15V, RI=100K Measure current into VDD	3		20	uA
I_VDD_Ops Opera	tion Current	VDD=16V, RI=100Kohm, V _{FB} =3V	2.3			mA
UVLO(Enter) VDI	Under Voltage Lockout Enter		8.8 9.8	10.8		V
UVLO(Exit) VDD	Under Voltage Lockout Exit (Startup)		15.5 16	.5 17.5		V
OVP(Latch)	VDD Over Voltage Latch Trigger	26.5	√	28	29.5	V
OVP(De-Latch)	VDD Latch Release Voltage Threshold		<u>></u>	7.5		V
I(Vdd)_latch	VDD bleeding current at latch shutdown when VDD = 9V	Both		45		uA
T _D OVP	VDD OVP Debounce time	RI = 100Kohm		80		uSec
V _{DD} _Clamp V	_{DD} Zener Clamp Voltage	$RI = 100 \text{ Kohm}, I(V_{DD}) = 5 \text{ mA}$	35			V
T_Softstart	Soft Start Time			3		mSec
Feedback Input Se	ection(FB Pin)					
A_{VCS}	PWM Input Gain	$\Delta V_{FB} / \Delta V_{cs}$	2.8			V/V
V _{FB} Open V	FB Open Voltage	VDD = 16V		6.2	V	
I _{FB} _Short	FB pin short circuit current	Short FB pin to GND, measure current	0.75			mA
V _{TH} _0D	Zero Duty Cycle FB Threshold Voltage	VDD = 16V, RI=100Kohm	0.95			V
V _{TH} _BM	Burst Mode FB Threshold Voltage			1.6		V
V _{TH} _PL	Power Limiting FB Threshold Voltage			4.4		V
T _D _PL Power	limiting Debounce Time	VDD = 16V, RI=100Kohm	80			mSec
Z _{FB} _IN Input	Impedance			9.0		Kohm
Current Sense Inp	out(Sense Pin)					
T_blanking	Sense Input Leading Edge Blanking Time	RI = 100Kohm		300		nSec
Z _{SENSE} _IN Sense	Input Impedance			30		Kohm
T _D OC Over	Current Detection and Control Delay	CL=1nf at GATE, RI=100Kohm	70			nSec
V _{TH} _OC_0 Current	Limiting Threshold at No Compensation	VDD = 16V, I(VIN) = 0uA, RI=100Kohm	0.85 0.9	0 0.95		V

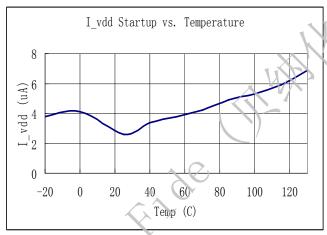


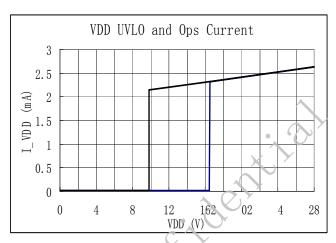
V _{TH} _OC_1 Current		VDD = 16V, I(VIN) =	0.80			V		
	Threshold at	150uA, RI=100Kohm						
	Compensation							
Oscillator								
Fosc	Normal Oscillation Frequency	RI = 100Kohm	60	65	70	KHZ		
Δf_Temp	Central Frequency Temperature Stability	VDD = 16V, RI=100Kohm, -20°C to	3			%		
		100 °C				HIV		
Δf_{VDD}	Central Frequency Voltage Stability	VDD = 12-28V, RI=100Kohm	3			%		
RI_range	Operating RI Range		50	100	250	Kohm		
V RI open	RI open voltage	VDD = 16V		2.0	200	V		
F BM	Burst Mode Base	VDD = 16V,	20			KHZ		
1_2111	Frequency	RI=100Kohm		. 0		12112		
Gate Drive Outpu				76	,			
VOL	Output Low Level	VDD = 16V, $Io = 20 mA$			0.3	V		
VOH	Output High Level	VDD = 16V, Io = 20 mA	11	>		V		
VG Clamp Output			-	16.5		V		
,,	Voltage Level	6	2			·		
Tr	Output Rising Time	VDD = 16V, CL = 1nf	<u> </u>	120		nSec		
Tf	Output Falling Time	VDD = 16V, CL = 1nf		50		nSec		
Over Temperatur	Over Temperature Protection							
I RT	Output Current of RT	VDD = 16V,	70			uA		
_	pin	RI=100Kohm						
V _{TH} _OTP OTP	Threshold	VDD = 16V	1.015	1.065 1	.11 5	V		
_	Voltage	RI=100Kohm						
$V_{TH}_OTP_off$	OTP Recovery	VDD = 16V,	1.16	5		V		
(Version V Only)	Threshold Voltage •	RI=100Kohm						
V _{TH} _RT_latch	RT Input Latch			0.6		V		
(Version V Only)	Threshold Voltage)						
T_{D} OTP	OTP De-bounce Time	VDD = 16V,	100			uSec		
	70'	RI=100Kohm						
V_RT_Open	RT Pin Open Voltage	VDD = 16V,	3.7			V		
	\mathcal{C}	RI=100Kohm						
Frequency Shuffli					ı	T		
Δf_OSC	Frequency	RI=100Kohm -3			3	%		
	Modulation range							
- al ar	Base frequency							
Freq Shuffling	Shuffling Frequency	RI = 100Kohm		32	1	HZ		

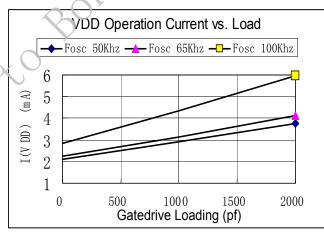


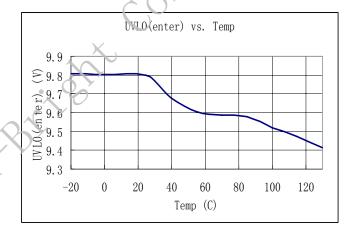
CHARACTERIZATION PLOTS

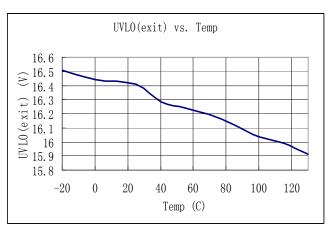






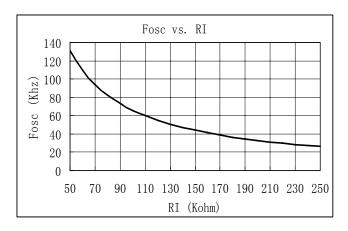


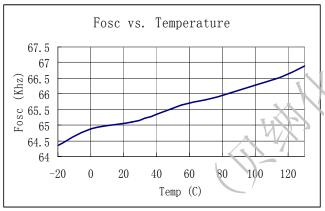


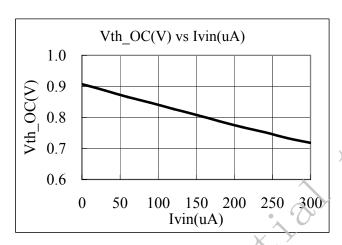


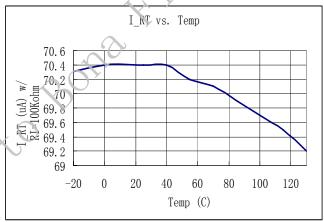


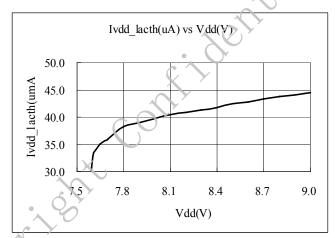














OPERATION DESCRIPTION

OB2279 is a highly integrated PWM controller IC optimized for offline flyback converter applications with requirement in latch shutdow n or auto recovery. The extended burst mode control greatly reduces the standby power consumption and helps the design easily meet the international power conservation requirements.

Startup Current and Start up Control

Startup current of OB227 9 is designed to be ver y low so that VDD could be charged up above UVLO(exit) threshold lev el and device starts up quickly. A large value startup resistor can therefore be used to mini mize the power loss yet reliable startup in application. For a typical AC/DC adaptor with universal input range design, a 2 M Ω , 1/8 W startup resistor could be used together with a VDD capacitor to provide a fast startup a nd yet low power dissipation design solution.

• Operating Current

The Operating current of OB2279 is low at 2.3mA. Good efficiency is achieved with OB2279 low operating cu rrent together with extended burst mode control schemes.

Frequency shuffling for EMI improvement

The frequency Shuffli ng/jittering (switching frequency modulation) is implemented in OB2279. The oscillation frequency is modulated with a internally generated random source so that the tone energy is evenly spread out. The spread spectrum minimizes the conduction band EMI and therefore eases the sy stem design in meeting stringent EMI requirement.

Burst Mode Operation

At zero load or light load condition, most of the switching mode power power dissipation in a supply is from switching loss on the MOSFET transistor, the core loss of the transformer and the loss on the snubber circuit. The magnitude of power loss is in propor tion to t he num ber of switching events within a fixed period of tim Reducing switching event s leads to the e reduction on the power loss and thus conserves the energy. OB2279 self adjusts the switching m ode according to the loading conditi on. At fro m no load to light/medium load condition, the FB input drops below burst mode threshold level. D evice enters Burst Mode control. The Gate drive output switches only when VDD voltage drops below a preset level and FB input is active to output an on state. Otherwise the gate drive re mains at off state to

minimize the switching loss thus reduce the standby power consumption to the greatest extend. The nature of high f requency switching also reduces the audio noise at any loading conditions.

Oscillator Operation

A resistor connected between RI and G ND sets the constant current source to charge/discharge the internal cap and thus the PWM oscillator frequency is determ ined. The relationship between RI and switching frequency fol lows the below equation within the specified RI in Kohm range at nom inal loading operational condition.

$$F_{OSC} = \frac{6500}{RI(Kohri)}(Khz)$$

• Current S ensing and Leading Edge Blanking (LEB)

Cycle-by-Cycle current lim iting is offered in OB2279 curr ent mode PWM control. The switch current is detected by a sense resistor into the sense pin. An internal leading edge blanking circuit chops off the sense voltage spike at initial MOSFET on state due to snubber dio de reverse recovery so that the external RC filtering on sense input is no longer needed. The current lim it comparator is disabled and cannot turn off the external MOSFET during the blanking period. The PWM duty cycle is determined by the current sense input voltage and the FB input voltage.

• Internal Synchronized Slope Compensation

Built-in slope com pensation circuit adds voltage ramp onto the current sense input voltage for PWM generation. This greatly improves the close loop stability at CCM and pr events the sub-harm onic oscillation and thus reduces the output ripple voltage.

Over Temperature P rotection with Latch Shutdown(Only to T and L version)

A NTC resi stor in series with a regular resistor should connect between RT and GND for temperature sensing and protection. NTC resi stor value becomes lower when the ambient temperature rises. With the fixed internal current I_{RT} flowing through the resistors, the voltage at RT pin becomes low er at high tem perature. The internal OTP circuit is trigge red and shutdown the MOSFET when the sensed input voltage is lower than V_{TH} OTP. OTP is a latched shutdown.

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RT Pin Used as Latch Shutdown Input **Control**

RT pin coul d also be used as a control inp ut to implement system latch shutdown function. An exa mple is to i mplement sy stem OVP protection with a latch shutdown function through a photo couple r and affiliated circuits. When OVP detection signal connected to RT is lower than V_{TH} OTP for Version T/L device, (or V_{TH} OT Latch for Version V), OB2 279 co ntrols system into latch shutdown. The recovery AC/DC system could only start by resetting internal latch when VDD voltage drops below VDD Delatch value. This cou ld be ach unplugging/re-plugging of AC source in AC startup configuration.

Gate Drive

OB2279 Gate is connected to the Gate of an external MOSFET for power swit ch control. Too weak the g ate drive str ength results in higher conduction and switch loss of MOSFET while too strong gate drive output compromises the EMI. Good tradeoff is achiev ed through the built-in totem pole gate drive d esign with r ight output strength and dead tim e control. The lo widle loss and good EMI sy stem design is easi er to achieve with this dedicated control schem e. An internal a gate put. 16.5V clamp is added for MOSFET gate protection

Good system reliability is achieved with OB2279's rich protection features including C ycle-by-Cycle current limiting (OCP), Over Load Protection (OLP) with auto-recovery (V and T version) or latch shutdown(L version), over temperature protection (OTP) with auto-recovery (V version) or latch shutdown(T and L version), on-chip VDD over voltage protection (OVP) with latch shutdown and under voltage lockout (UVLO).

VDD O VP protection is a latched shutdown in OB2279.

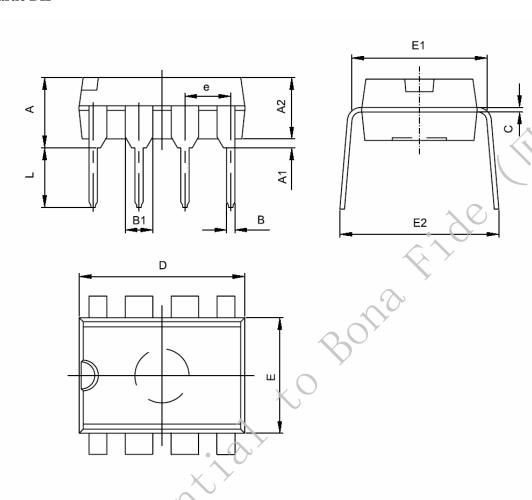
The OCP thr eshold value is self adjusted lower at higher curren t into VIN p in. This OC P threshold slope adjustment helps to compensate the increased output power lim it at higher AC voltage caused by inherent Over-Current sensing and control delay. A constant out put p ower lim it is achieved with recommended OCP compensation scheme.

At output o verload condition, FB vo ltage is set higher. When FB input exceeds power li mit threshold value for more than 80mS, control circuit reacts to turnoff the power MOSFET. This is so called OLP shutdown. It is either auto-recovery or latched shutdown depending on version of OB2279. Similarly, c ontrol circuit shutdowns the power MOSFET when an Over Temperature condition is detected. This shutdown is either auto-recovery or latched depending on version of OB2279 been used. pplied with transformer auxiliar winding output. It is clamped when VDD is higher than 35V. MOSFET is shut down when VDD drops below UVLO(enter) lim it and device enters power on start-up sequence therea



PACKAGE MECHANICAL DATA

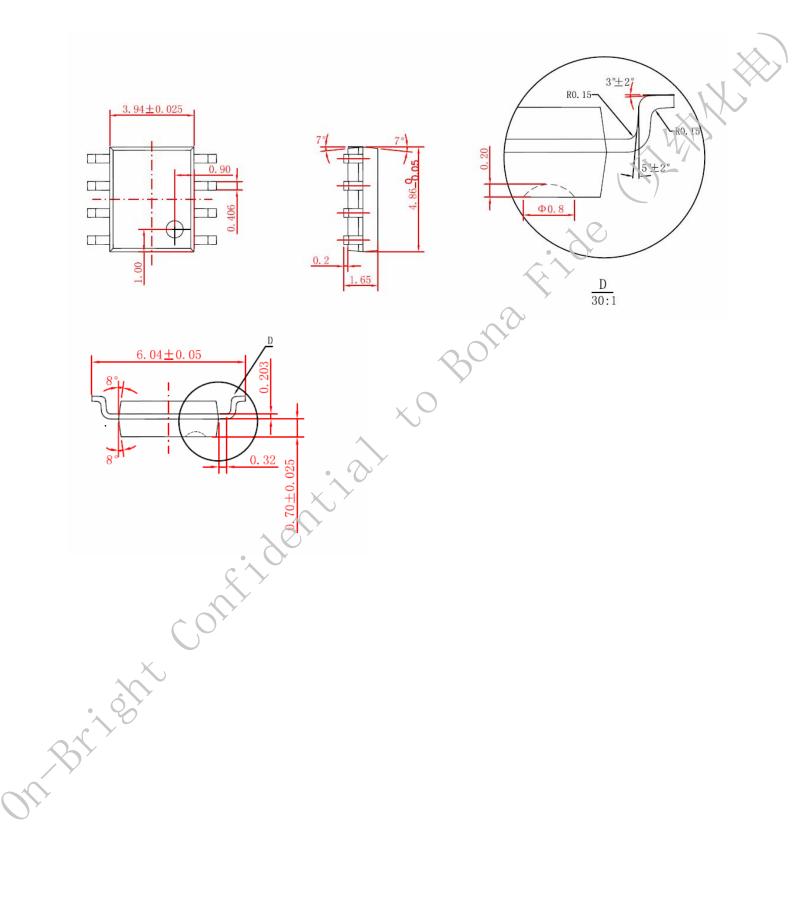
8-Pin Plastic DIP



Obl	Dimensions In Millimeters		Dimensions	s In Inches	
Symbol	Min	Max	Min	Max	
A	3.710	4.310	0.146	0.170	
A1	0.510	0.020			
A2	3.200	3.600	0.126	0.142	
В	0.360	0.560	0.014	0.022	
B1	1.52	24(TYP)	0.06	0(TYP)	
С	0.204	0.360	0.008 0.014 0.354 0.370		
D	9.000	9.400			
E	6.200	6.600	0.244 0.260		
E1	7.62	20(TYP)	0.300(TYP)		
е	2.54	10(TYP)	0.100(TYP)		
L	3.000	3.600	0.118	0.142	
E2	8.200	9.400	0.323	0.370	



8-Pin Plastic SOP



IMPORTANT NOTICE

RIGHT TO MAKE CHANGES

On-Bright Electronics Corp. reserv es the right to m ake corrections, m odifications, enhancements, improvements and other changes to its products and ser vices at any time and to disconti nue any product or service without notice. Customers should obtain the latest relevant information before placing orders and should verify that such information is current and complete.

WARRANTY INFORMATION

On-Bright Electronics Corp. warrants p erformance of its ha rdware products to the speci fications applicable at the time of sale in accordance with its standard warranty. Testing and other quality control techniques are used to the extent it deems necessary to support this warranty. Except where mandated by government requirements, testing of all parameters of each product is not necessarily performed.

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